

L Number	Hits	Search Text	DB	Time stamp
7	54	257/\$.cccls. and capacitor and pillar and (metal copper aluminum) same (storage lower) adj (electrode node)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/26 08:38
-	399	semiconductor and DRAM and capacitor same pillar	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/25 14:43
-	9	("4252579" "4833516" "5027172" "5055898" "5177576" "5316962" "5319235" "5350941" "5498584").PN.	USPAT	2002/09/25 13:43
-	272	(257/308).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/25 14:46
-	256	((257/308).CCLS.) and @ad<=20001226	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/25 14:50
-	241	((((257/308).CCLS.) and @ad<=20001226) not (semiconductor and DRAM and capacitor same pillar))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/25 15:48
-	12	5481127.URPN.	USPAT	2002/09/25 15:03
-	4	("5023683" "5208479" "5218219" "5318920").PN.	USPAT	2002/09/25 15:05
-	26	5023683.URPN.	USPAT	2002/09/25 15:11
-	2	("4785337" "4855801").PN.	USPAT	2002/09/25 15:17
-	4	("5023683" "5208479" "5218219" "5318920").PN.	USPAT	2002/09/25 15:17
-	12	5481127.URPN.	USPAT	2002/09/25 15:18
-	445	(257/309).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/25 15:48
-	341	((257/309).CCLS.) not (((((257/308).CCLS.) and @ad<=20001226) not (semiconductor and DRAM and capacitor same pillar)) (semiconductor and DRAM and capacitor same pillar))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/25 15:49
-	298	((((257/309).CCLS.) not (((((257/308).CCLS.) and @ad<=20001226) not (semiconductor and DRAM and capacitor same pillar)) (semiconductor and DRAM and capacitor same pillar)))) and @ad<=20001226	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/25 16:04
-	51	257/\$.cccls. and capacitor and capacitor adj dielectric and metal same storage adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/26 08:36
-	196	capacitor and semiconductor and storage adj (node electrode) same pillar	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/25 16:24

-	43	(capacitor and semiconductor and storage adj (node electrode) same pillar) not ((semiconductor and DRAM and capacitor same pillar) (((257/308).CCLS.) and @ad<=20001226) not (semiconductor and DRAM and capacitor same pillar)) (((257/309).CCLS.) not ((((257/308).CCLS.) and @ad<=20001226) not (semiconductor and DRAM and capacitor same pillar)) (semiconductor and DRAM and capacitor same pillar))) (257/\$.cccls. and capacitor and capacitor adj dielectric and metal same storage adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/25 16:25
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